

## ABSTRACT OF THE DISCLOSURE

A magnetic memory device, in which a tunnel magneto resistance element that establishes a connection between a write word line (first interconnection) and a bit line (second  
5 interconnection) is provided within a region in which the write word line and the bit line cross in a grade-separated manner. The magnetic memory device comprises a through hole that is provided in such a manner that is insulated from the write word line and also extending through the write word line so as  
10 to establish a connection between the tunnel magneto resistance element and a second landing pad (interconnection layer) lower than the write word line, and a contact that is formed in the through hole through a side wall barrier film so as to establish a connection between the tunnel magneto  
15 resistance element and the second landing pad.

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